

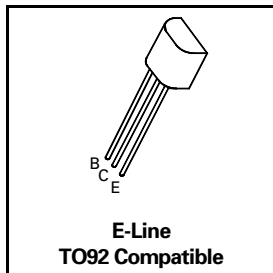
NPN SILICON PLANAR MEDIUM POWER TRANSISTOR

FXT451

ISSUE 1 – SEPT 93

FEATURES

- * 60 Volt V_{CEO}
- * 1 Amp continuous current
- * $P_{tot} = 1$ Watt



REFER TO ZTX451 FOR GRAPHS

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	2	A
Continuous Collector Current	I_C	1	A
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	1	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	80			V	$I_C=100\mu A, I_E=0$
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	60			V	$I_C=10mA, I_B=0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E=100\mu A, I_C=0$
Collector Cut-Off Current	I_{CBO}			0.1	μA	$V_{CB}=60V, I_E=0$
Emitter Cut-Off Current	I_{EBO}			0.1	μA	$V_{EB}=4V, I_C=0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.35	V	$I_C=150mA, I_B=15mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1.1	V	$I_C=150mA, I_B=15mA^*$
Static Forward Current Transfer Ratio	h_{FE}	50 10		150		$I_C=150mA, V_{CE}=10V^*$ $I_C=1A, V_{CE}=10V^*$
Transition Frequency	f_T	150			MHz	$I_C=50mA, V_{CE}=10V$ $f=100MHz$
Output Capacitance	C_{obo}			15	pF	$V_{CB}=10V, f=1MHz$



LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.